

Silicon PNP Power Transistors

2SA913 2SA913A

DESCRIPTION

- With TO-220 package
- Complement to type 2SC1913/1913A
- Large collector power dissipation
- High V_{CE0}

APPLICATIONS

- Audio frequency high power driver

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

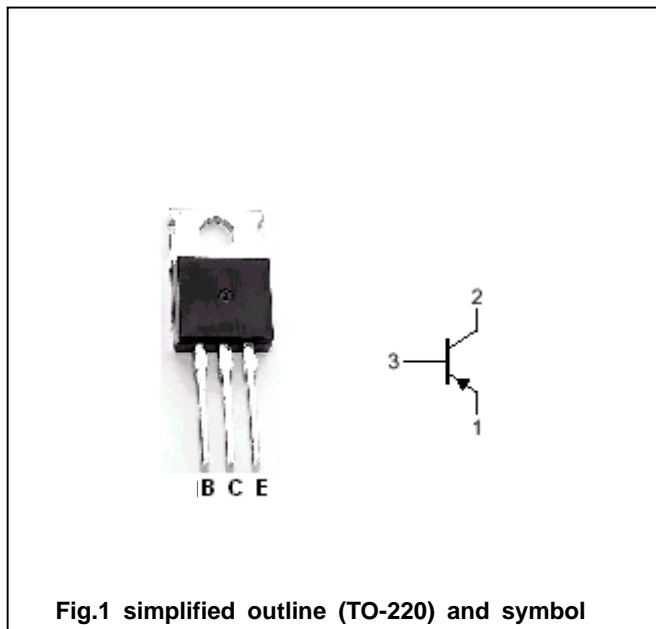


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA913	-150	V
		2SA913A	-180	
V_{CEO}	Collector-emitter voltage	2SA913	-150	V
		2SA913A	-180	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1	A
I_{CM}	Collector current-peak		-1.5	A
P_C	Collector power dissipation	$T_C=25$	15	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Base-emitter breakdown voltage	2SA913	I _C =-0.1mA, I _B =0	-150			V
		2SA913A		-180			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-10 μA, I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	2SA913	I _C =-0.5A; I _B =-50mA			-1.0	V
		2SA913A	I _C =-0.3A; I _B =-30mA			-1.5	
V _{BEsat}	Base-emitter saturation voltage	2SA913	I _C =-0.5A; I _B =-50mA			-1.5	V
		2SA913A	I _C =-0.3A; I _B =-30mA				
I _{CBO}	Collector cut-off current		V _{CB} =-120V; I _E =0			-1	μA
I _{EBO}	Emitter cut-off current		V _{EB} =-4V; I _C =0			-1	μA
h _{FE-1}	DC current gain		I _C =-150mA; V _{CE} =-10V	65		330	
h _{FE-2}	DC current gain		I _C =-500mA; V _{CE} =-5V	50			
C _{OB}	Output capacitance		I _E =0; V _{CB} =-100V; f=1MHz			15	pF
f _T	Transition frequency		I _C =50mA; V _{CE} =-10V		120		MHz

◆ h_{FE-1} Classifications

P	Q	R	S
65-110	90-155	130-220	185-330

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PACKAGE OUTLINE

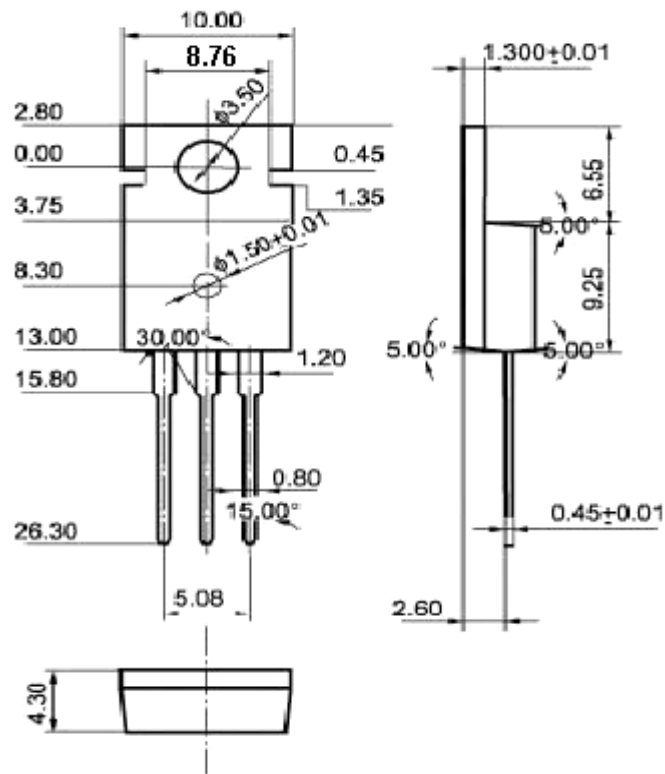


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)